THE DATASHEET OF

BCP5616TA

SOT223 NPN SILICON PLA
MEDIUM POWER TRANSIS

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FEATURES

- * Suitable for AF drivers and output s
- * High collector current and Low $V_{CE(s}$

COMPLEMENTARY TYPE – BCP53

PARTMARKING DETAILS – BCP56
BCP56 –
BCP56 –

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at T_{amb}=25°C
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MI
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	10
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	
Static Forward Current Transfer Ratio	h_{FE} BCP56-10 BCP56-16	40 25 63 10
Transition Frequency	f_T	

*Measured under pulsed conditions. Pulse